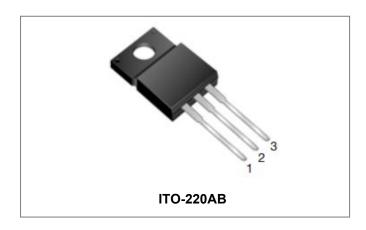






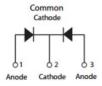
STF20H100C SCHOTTKY RECTIFIER



Features

- 175 °C T_J operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage	V _{RRM} V _{RWM}	-	100	V
DC Blocking Voltage	VR		100	•
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=105°C, rectangular wave form	10(Per Leg) 20(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	150	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (Per Leg)*	V_{F1}	@ 5A, Pulse, T _J = 25 °C @ 10A, Pulse, T _J = 25 °C	0.62 0.72	- 0.80	V
	V_{F2}	@ 5A, Pulse, T _J = 125 °C @ 10A, Pulse, T _J = 125 °C	0.52 0.60	- 0.70	V
Reverse Current(Per Leg)*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	1	100	uA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	0.3	-	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	420	-	pF

Pulse width < 300 μs, duty cycle < 2%

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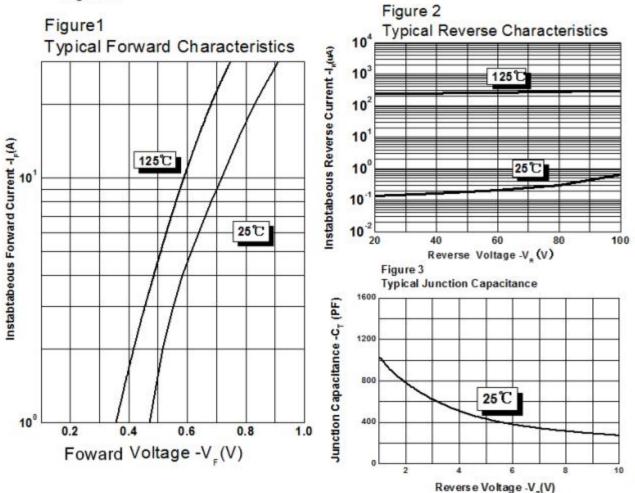


Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T_{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case(Per Leg)	$R_{ heta JC}$	DC operation	5	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

Ratings and Characteristics Curves





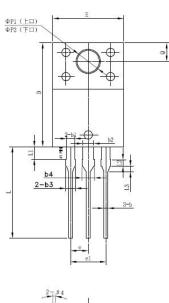
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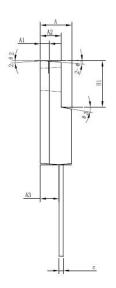






Mechanical Dimensions ITO-220AB







CVMDOL	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.30	4.50	4.70		
A1	1.10	1.30	1.50		
A2	2.80	3.00	3.20		
A3	2.50	2.70	2.90		
Ь	0.50	0.60	0.75		
b1	1.10	1.20	1.35		
b2	1.50	1.60	1.75		
b3	1.20	1.30	1.45		
b4	1.60	1.70	1.85		
С	0.50	0.60	0.75		
D	14.80	15.00	15.20		
E	9.96	10.16	10.36		
е		2.55			
e1		5.10			
H1	6.50	6.70	6.90		
L	12.70	13.20	13.70		
L1	1.60	1.80	2.00		
L2	0.80	1.00	1.20		
L3	0.60	0.80	1.00		
ΦP1(上□)	3.30	3.50	3.70		
ΦP2 (下口)	2.99	3.19	3.39		
Q	2.50	2.70	2.90		
Θ1		5°			
Θ2		4°			
Θ3		10°			
Θ4		5°			
Θ5		5°			

Marking Diagram



Where XXXXX is YYWWL

 ST
 = Device Type

 F
 = Package type

 20
 = Forward Current (20A)

 H
 = Tj 175°C

 100
 = Reverse Voltage (100V)

 C
 = Configuration

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Fnovy regin I II -94\/_0

Tube Specification



Ordering Information

Device	Package	Shipping
STF20H100C	ITO-220AB (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

- China Germany Korea Singapore United States
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